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### Publications (See citations in [Google Scholar](#))

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1. Q. Qian, R. Zu, Q. Ji, G. S. Jung, K. Zhang, Y. Zhang, M. J. Buehler, J. Kong, V. Gopalan and S. Huang, "Chirality-Dependent Second Harmonic Generation of MoS<sub>2</sub> Nanoscroll with Enhanced Efficiency," *ACS Nano*, accepted (<https://pubs.acs.org/doi/10.1021/acsnano.0c05189>)
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  10. Q. Qian, G. Li, Y. Jin, J. Liu, Y. Zou, K. Jiang, S. Fan, and Q. Li, "Trap-State-Dominated Suppression of Electron Conduction in Carbon Nanotube Thin-Film Transistors," *ACS Nano* **8**, 9597, 2014
  11. Q. Qian, J. Liu, Q. Li, Y. Zou, Y. Jin, G. Li, K. Jiang, and S. Fan, "Modeling and optimization of ambipolar graphene transistors in the diffusive limit," *J. Appl. Phys.* **114**, 164508, 2013
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